

## Silicon NPN Power Transistors

2SC2239

**DESCRIPTION**

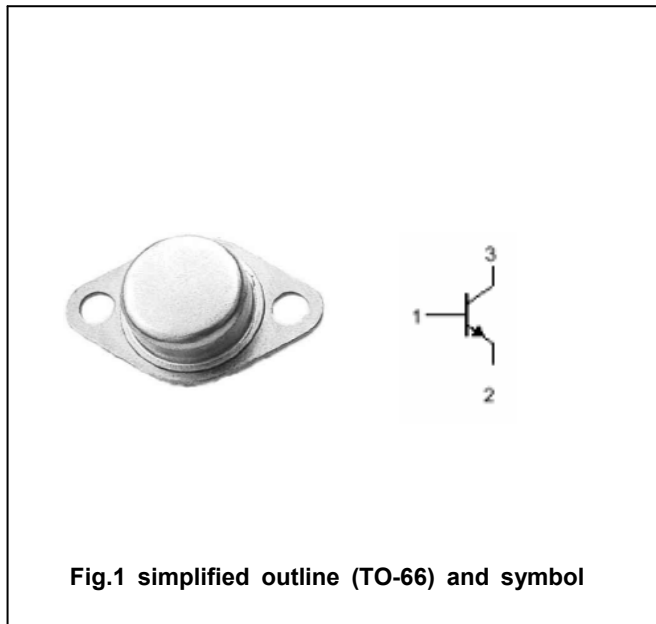
- With TO-66 package
- Complement to type 2SA969
- High breakdown votage

**APPLICATIONS**

- Power amplifier applications
- Driver stage amplifier applications

**PINNING (See Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=25□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	160	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	160	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		1.5	A
I <sub>E</sub>	Emitter current		-1.5	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25□	25	W
T <sub>j</sub>	Junction temperature		150	□
T <sub>stg</sub>	Storage temperature		-55~150	□

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA; I <sub>B</sub> =0	160			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =500mA; I <sub>B</sub> =50mA			1.5	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =500mA; V <sub>CE</sub> =5V			1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =160V; I <sub>E</sub> =0			1.0	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =100mA; V <sub>CE</sub> =5V	70		240	
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V, f=1MHz		25		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =100mA; V <sub>CE</sub> =10V		100		MHz

◆ h<sub>FE</sub> Classifications

O	Y
70-140	120-240

PACKAGE OUTLINE

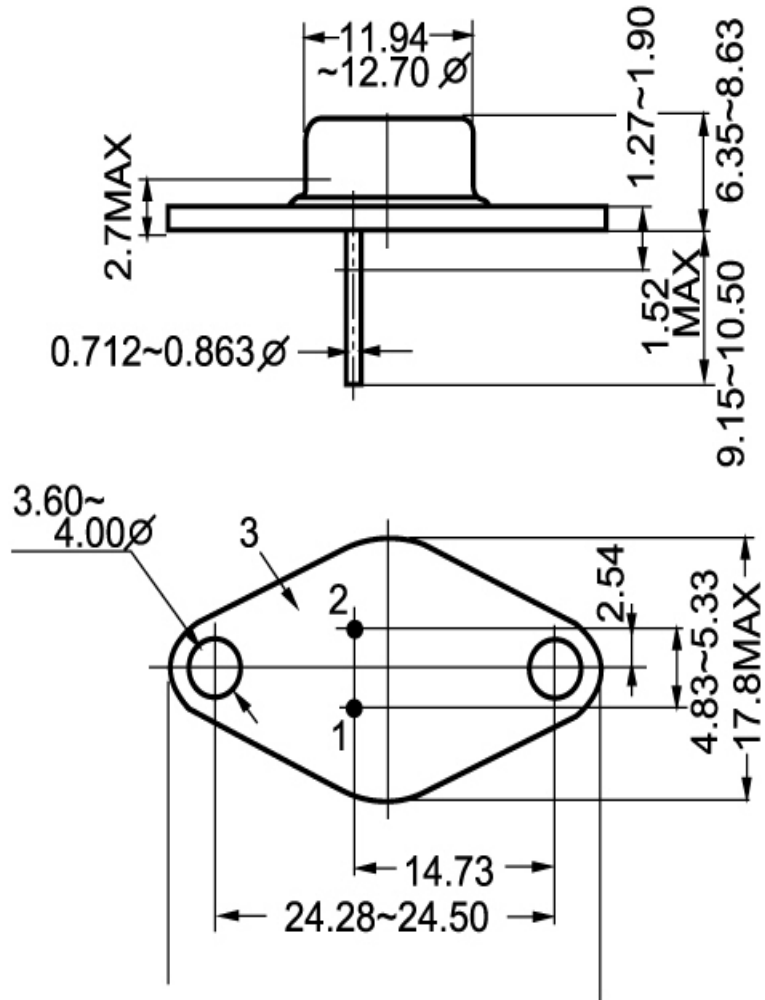


Fig.2 Outline dimensions